

# 2SB1317

## Silicon PNP triple diffusion planar type

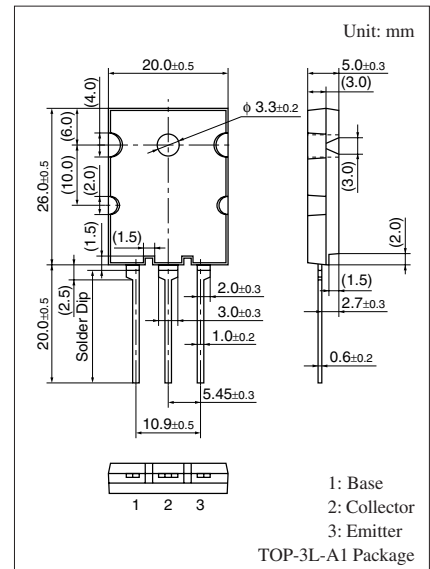
For high power amplification  
Complementary to 2SD1975

### ■ Features

- Excellent collector current  $I_C$  characteristics of forward current transfer ratio  $h_{FE}$
- Wide safe operation area
- High transition frequency  $f_T$
- Optimum for the output stage of a Hi-Fi audio amplifier

### ■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	-180	V
Collector-emitter voltage (Base open)	$V_{CEO}$	-180	V
Emitter-base voltage (Collector open)	$V_{EBO}$	-5	V
Collector current	$I_C$	-15	A
Peak collector current	$I_{CP}$	-25	A
Collector power dissipation	$P_C$	150	W
	$T_a = 25^\circ\text{C}$	3.5	
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$



### ■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Base-emitter voltage	$V_{BE}$	$V_{CE} = -5\text{ V}, I_C = -8\text{ A}$			-1.8	V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = -180\text{ V}, I_E = 0$			-50	$\mu\text{A}$
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = -3\text{ V}, I_C = 0$			-50	$\mu\text{A}$
Forward current transfer ratio	$h_{FE1}$	$V_{CE} = -5\text{ V}, I_C = -20\text{ mA}$	20			—
	$h_{FE2}^*$	$V_{CE} = -5\text{ V}, I_C = -1\text{ A}$	60		200	
	$h_{FE3}$	$V_{CE} = -5\text{ V}, I_C = -8\text{ A}$	20			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10\text{ A}, I_B = -1\text{ A}$			-2.5	V
Transition frequency	$f_T$	$V_{CE} = -5\text{ V}, I_C = -0.5\text{ A}, f = 1\text{ MHz}$		20		MHz
Collector output capacitance (Common base, input open circuited)	$C_{ob}$	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$		200		pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*: Rank classification

Rank	Q	S	P
$h_{FE2}$	60 to 120	80 to 160	100 to 200

